

AMENDMENT

IN THE CLAIMS:

Please amend the claims as follows:

1. (Original) A manufacturing method of a semiconductor device, comprising the steps of:
depositing on a substrate a dielectric film made of fluorine-added carbon;
forming on the dielectric film a protective layer comprising a nitrogen-added silicon carbide film; and
depositing on the protective layer a thin film serving as a hardmask made of oxygen-added silicon carbide by a plasma containing active species of silicon, carbon, and oxygen.
2. (Currently amended) The manufacturing method according to claim 1, wherein
the plasma containing active species of silicon, carbon, and oxygen is ~~a plasma~~ obtained by activating a gas of an organic silicon compound and an oxygen gas.
3. (Currently amended) The manufacturing method according to claim 1, wherein
the step of forming the protective layer includes the sub-steps of:
depositing on the dielectric film a silicon carbide film by a second plasma containing active species of silicon and carbon; and
depositing on the silicon carbide ~~film~~ a film the nitrogen-added silicon carbide film by a third plasma containing active species of silicon, carbon, and nitrogen.
4. (Currently amended) The manufacturing method according to claim 1, wherein
the step of forming the protective layer includes the sub-steps of:
depositing on the dielectric film a silicon carbide film by a second plasma obtained by activating a gas of an organic silicon compound; and
depositing on the silicon carbide ~~film~~ a film the nitrogen-added silicon carbide film by a third plasma containing active species of an organic silicon compound and active species of nitrogen.

5. (Currently amended) The manufacturing method according to claim 1, further comprising the steps of:

forming on the thin film serving as a ~~hardmask~~ the hardmask, a resist film having a ~~specific~~ first pattern;

etching the thin film by a second plasma through the resist film to obtain a ~~hardmask~~ the hardmask having a second pattern corresponding to ~~that of the resist film~~ the first pattern; and

etching the dielectric film by a third plasma through the hardmask.

6-12. (Canceled)